

# SANYO Semiconductors DATA SHEET

# N-Channel Silicon MOSFET

# SCH1411 — General-Purpose Switching Device Applications

#### **Features**

- · Low ON-resistance.
- · High-speed switching.
- · 4V drive.

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		2.0	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	8.0	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			1.1:4
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	30			V
Zero-Gate Voltage Drain Current	IDSS	VDS=30V, VGS=0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=1A	1.2	2.0		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =1A, V <sub>G</sub> S=10V		130	170	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.5A, V <sub>G</sub> S=4V		205	285	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		120		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		30		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		15		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		6		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		4		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		17		ns
Fall Time	tf	See specified Test Circuit.		5		ns

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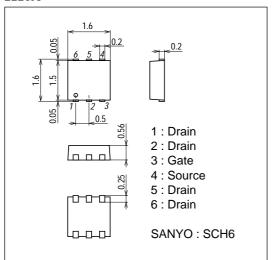
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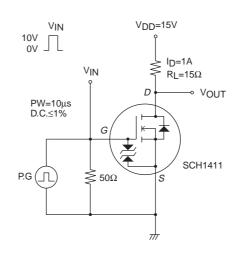
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =2.0A		3.6		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =2.0A		0.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =2.0A		0.5		nC
Diode Forward Voltage	VSD	IS=2.0A, VGS=0		0.88	1.2	V

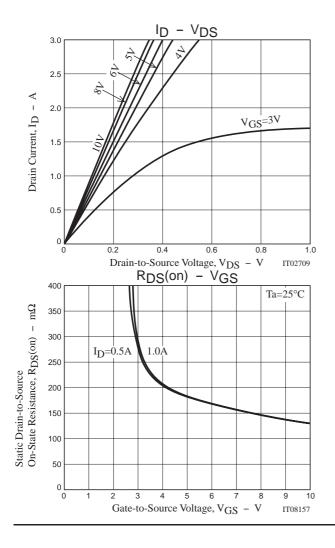
## **Package Dimensions**

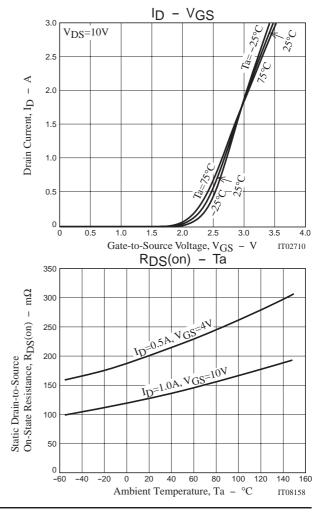
unit : mm 2221A

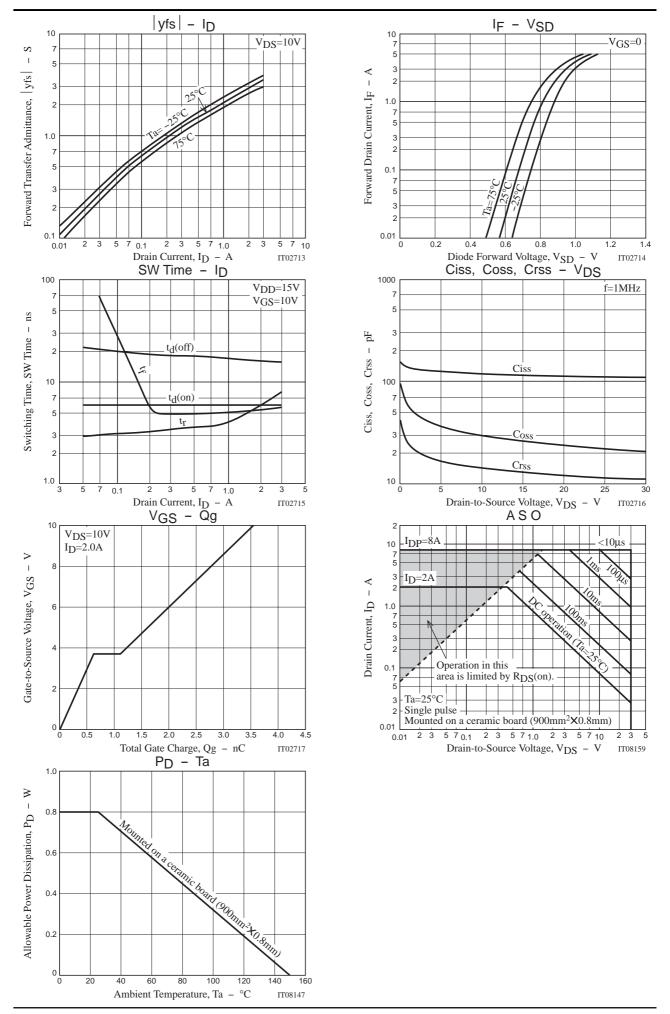


### **Switching Time Test Circuit**









Note on usage: Since the SCH1411 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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